

EPITAXIAL PLANAR PNP TRANSISTOR

LOW COLLECTOR SATURATION VOLTAGE LARGE CURRENT

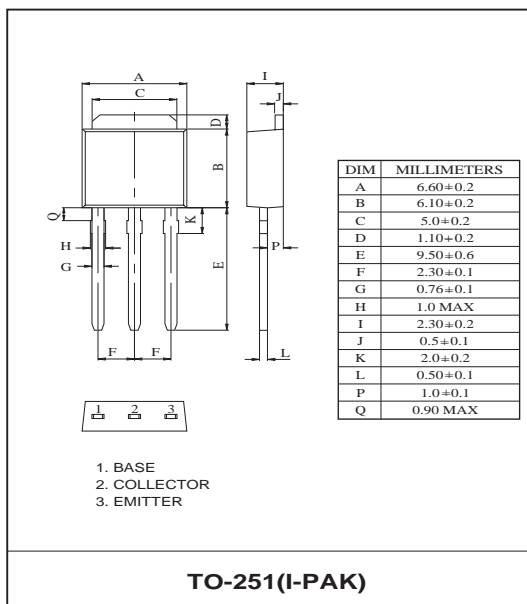
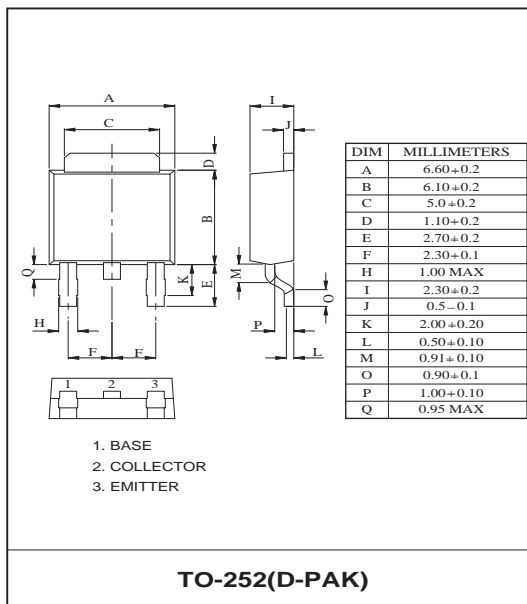
FEATURES

- High Power Dissipation : $P_C = 1.3W(T_a = 25^\circ C)$

MAXIMUM RATING ($T_a = 25^\circ C$)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Base Voltage		V_{CBO}	-60	V
Collector-Emitter Voltage		V_{CEO}	-60	V
Emitter-Base Voltage		V_{EBO}	-7	V
Collector Current	DC	I_C	-5	A
	Pulse *	I_{CP}	-8	
Base Current		I_B	-1	A
Collector Power Dissipation	$T_a = 25^\circ C$	P_C	1.3	W
	$T_C = 25^\circ C$		15	
Junction Temperature		T_j	150	$^\circ C$
Storage Temperature Range		T_{stg}	-55 ~ 150	$^\circ C$

* $PW \leq 10ms$, Duty Cycle $\leq 50\%$



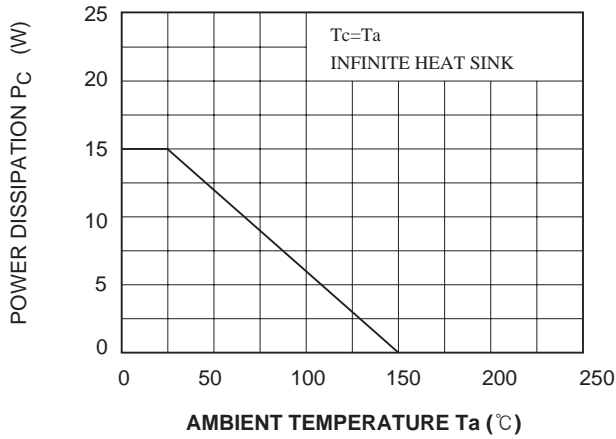
ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ C$)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		I_{CBO}	$V_{CB} = -50V, I_E = 0$	-	-	-10	μA
Emitter Cut-off Current		I_{EBO}	$V_{EB} = -7V, I_C = 0$	-	-	-10	μA
DC Current Gain *		h_{FE1}	$V_{CE} = -1V, I_C = -0.1A$	60	-	-	
		h_{FE2} (Note)	$V_{CE} = -1V, I_C = -2A$	160	-	400	
		h_{FE3}	$V_{CE} = -2V, I_C = -5A$	50	-	-	
Collector-Emitter Saturation Voltage *		$V_{CE(sat)}$	$I_C = -2A, I_B = -0.2A$	-	-0.14	-0.3	V
Base-Emitter Saturation Voltage *		$V_{BE(sat)}$	$I_C = -2A, I_B = -0.2A$	-	-0.9	-1.2	V
Switching Time	Turn On Time	t_{on}	<p style="text-align: center;">$-I_{B1} = I_{B2} = 0.2A$ DUTY CYCLE $\leq 1\%$</p>	-	0.15	1	μS
	Storage Time	t_{stg}		-	0.78	2.5	
	Fall Time	t_f		-	0.18	1	

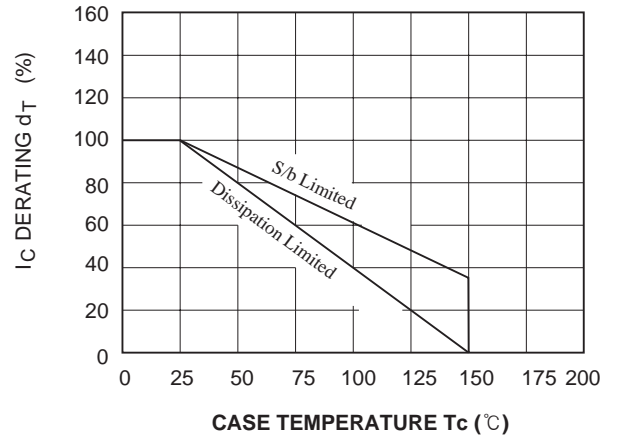
* Pulse test : $PW \leq 350 \mu S$, Duty Cycle $\leq 2\%$ Pulse

Note) $h_{FE}(2)$ Classification : O:160~320, Y:200~400.

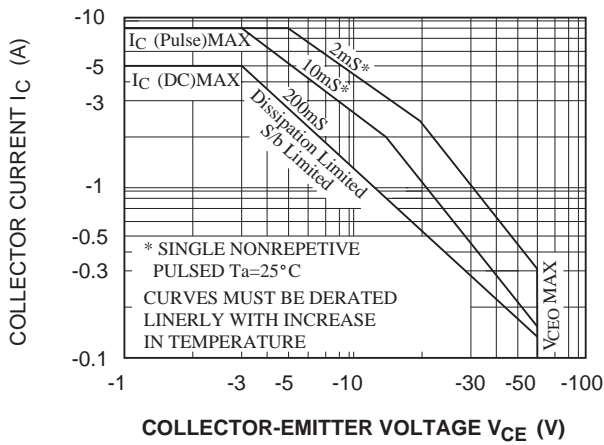
P_c - T_a



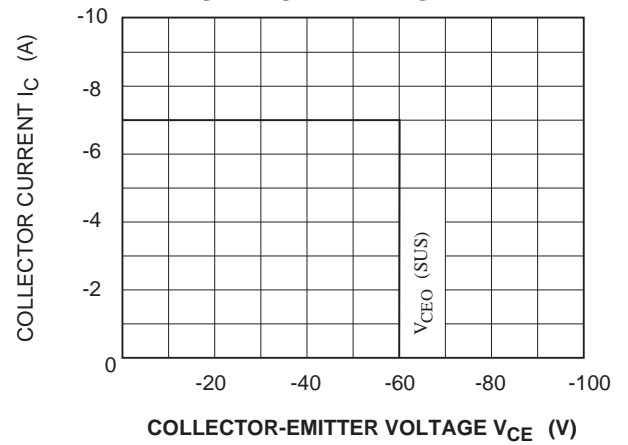
d_T - T_C



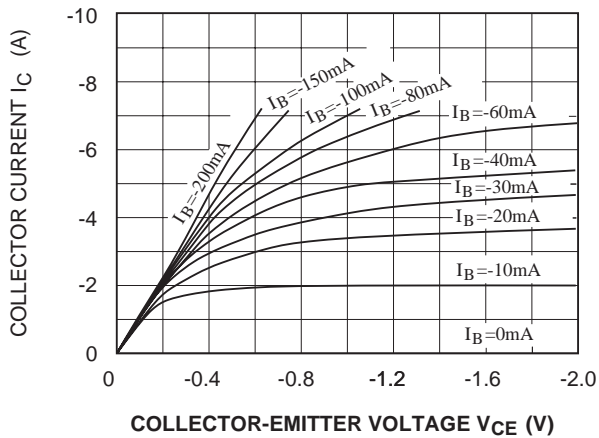
SAFE OPERATING AREA



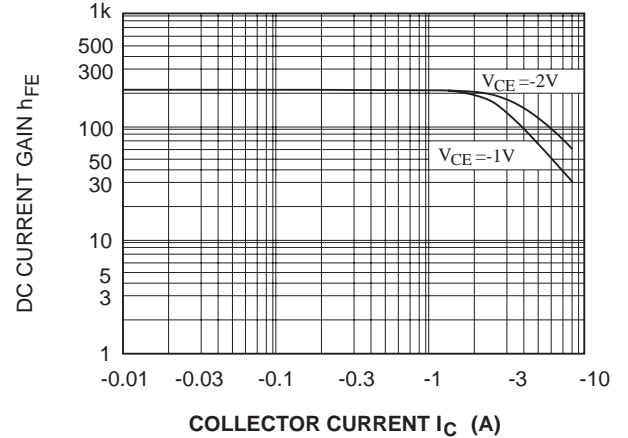
REVERSE BIAS SAFE OPERATING AREA



I_C - V_{CE}



h_{FE} - I_C





FTA1385D/I

